

5 é □ □ □ □ □ □ □ □ □ □ □ □ □ □

SOT23-3 .> // x P 3 « | • 'ož
6 CHANNEL MOSFET in a SOT23 -3 Plastic Package.

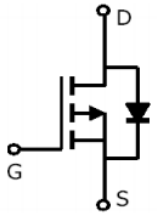
□ a □ □ □ □ □ □ □ □ □ □ □ □ □ □

$V_{DS} = -60V$; $I_D = -3A$
 $R_{DS(on)1} @ -10V$ 0 100m Ω (Type.83m Ω)
 $R_{DS(on)2} @ -4.5V$ 0 130m Ω (Type.100m Ω)
 —)í D }ož HF Product.

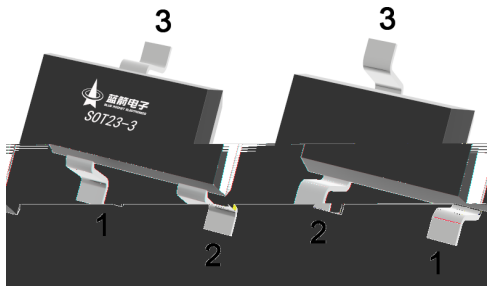
Đ ÷ □ □ □ □ □ □ □ □ □ □ □ □ □ □

6 = 3 • ĵ ú • ¼ož
PWM application & Load switch.

Ã W] Ô • □ □ □ □ □ □ □ □ □ □ □ □ □ □



• Ů - æ □ □ □ □ □ □ □ □ □ □ □ □ □ □



PIN1 y G PIN 2 y S PIN 3 y D

, M V □ □ □ □ □ □ □ □ □ □ □ □ □ □

• - ~ a øž
See Marking Instructions.

@ f Parameter	... Z Symbol	f › Rating	% y Unit
Drain–Source Voltage	V _{DSS}	-60	V
Gate–Body Leakage Voltage	V _{GSS}	±20	V
Drain Current – Continuous	I _D	-3	A
Pulsed Drain Current	I _{DM}	-16	A
Power Dissipation	P _D	1.4	W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 150	
Maximum Junction-to-Ambient	R _{θJA}	89	/W

□
 □

GS

@ f Parameter	... Z Symbol	y j Ú ^ Test Conditions	Â 4 › Min	Á ° › Typ	Â Ý › Max	% y Unit
Drain–Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V I _D =-250 A	-60	-65		V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} I _D =-250 A	-1	-1.6	-2.5	V
Static Drain–Source On–Resistance	R _{DS(on)}	V _{GS} =-10V I _D =-2A		83	100	m
		V _{GS} =-4.5V I _D =-1A		100	130	m
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-60V _{GS} V _{GS} =0V			-1.0	A
Gate-Body leakage current	I _{GSS}	V _{GS} =±20V V _{DS} =0V			±100	nA
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} =0V I _S =-1A T _J =25			-1.2	V
Gate resistance	R _g	f=1MHz		6.5		

Input CapalInput Ca552 3610.4958z56TJ 71RC03 Tm 0 Tc 0 Tw (g)Tj 1 0 Inp3resista2356.1 381.5iss03 Tm 0 Te(T)W

□ □ □ □ □ □ □ □ □ □

Rev.B Aug.-2025

